

Abstract of the Invention

In order to be able to detect an irradiation position of an electron beam matching a defect position and conduct composition analysis of a defect with high precision and high efficiency, in the present invention, when a composition analysis target defect is selected and irradiation conditions of the electron beam are set for EDX analysis, a low-resolution reference image of low resolution is acquired using the electron beam at a defect corresponding position corresponding to the position of this defect on a chip in the vicinity of a target chip including defects, and a low-resolution defect image of the same low resolution is next acquired at the defect position of the target chip. Then, by comparing these low-resolution images, the defect position is acquired, the electron beam is slanted and irradiated on this defect position to acquire a composition spectrum of the defect.